

Amendments to the Specification:

After the title, please insert the following paragraph:

This is a divisional application of U.S. Serial No. 10/111,382, filed May 1, 2002.

Please replace the paragraph beginning at page 1, line 4, with the following amended paragraph:

The present invention relates to a waste gas treating burner for use in a combustion-type waste gas treatment system for combusting harmful waste gases such as a deposition gas containing SiH₄ and a halogen-base gas ([CHF₄] CHF₃, C₂F₆, CF₄, etc.), which are emitted from semiconductor manufacturing system.

Please replace the paragraph beginning at page 1, line 10, with the following amended paragraph:

Semiconductor manufacturing system emits harmful waste gases such as a deposition gas containing SiH₄ and a halogen-base gas ([CHF₄] CHF₃, C₂F₆, CF₄, etc.), which should not be discharged directly into the atmosphere. It is therefore the general practice in the art to introduce such harmful waste gases into an abatement system where the waste gas is detoxified by way of combustion. According to the general waste gas treatment system, an auxiliary combustible gas is used to produce flames in a furnace for thereby combusting the waste gases.

Please replace the paragraph beginning at page 20, line 6, with the following amended paragraph:

The air C is guided into and held by the air chamber 22, and ejected substantially circumferentially as a strong swirling flow from the air ejection nozzles 25 defined in the inner circumferential surface of the first cylindrical body 12a into the first flame stabilizing zone 15a. The [e] waste gas A is guided into and held by the waste gas chambers 20, and ejected from the waste gas flame holes 23 defined in the lower surface of the plate 14 into the first flame stabilizing zone 15a. The primary auxiliary combustible gas B1 is guided into and held by the first auxiliary combustible gas chambers 21a, and ejected from the first auxiliary combustible gas flame holes 24 defined in the lower surface of the plate 14 into the first flame stabilizing zone 15a. The waste gas A and the primary auxiliary combustible gas B1 which are ejected, are mixed with the swirling air flow. When ignited by an ignition source, not shown, the mixed gases produce swirling flames, which are primary flames, along the inner circumferential surface of the first cylindrical body 12a. The flow rate of the air C is greater than a theoretical equivalent to the flow rate of the primary auxiliary combustible gas B1, so that the produced primary flames are fuel-lean combustion flames characterized by the lean fuel.

Please replace the paragraph beginning at page 33, line 8, with the following amended paragraph:

The present invention is useful in combusting and treating harmful waste gases such as a deposition gas containing SiH₄ and a halogen-base gas (([CHF₄] CHF₃, C₂F₆, CF₄, etc.), which are emitted from semiconductor manufacturing system.